In the Claims:

Please cancel claims 7-19 The claims are as follows.

1. (Original) A method of forming a semiconductor structure, the method comprising the steps of:

providing a substrate having a surface oriented on a first crystal plane that enables subsequent crystal planes for channels to be utilized;

forming a first transistor so that a sidewall of a first fin body forms a first channel and so that the sidewall of the first fin body is oriented on a second crystal plane to provide a first carrier mobility; and

forming a second transistor so that a sidewall of a second fin body forms a second channel and so that the sidewall of the second fin body is oriented on a third crystal plane to provide a second carrier mobility that is different from the first carrier mobility.

2. (Original) The method of claim 1, wherein the step of providing a substrate comprises the step of providing a silicon substrate having surface oriented on a {110} crystal plane.

3. (Original) The method of claim 1, wherein the step of forming a first transistor comprises the step of forming a first transistor so that the sidewall of the first fin body is oriented on a {n n m} plane and n and m are any integer, wherein the step of forming a second transistor comprises forming a second transistor so that the sidewall of the second fin body is oriented on a {a a b} plane and a and b are any integer such that the {n n m} plane and the {a a b} plane are not

equivalent by a symmetry transformation.

4. (Original) The method of claim 1, wherein the step of forming a first transistor comprises the step of forming one of a first p-channel FinFET (PFET) and a first n-channel FinFET (NFET), wherein the step of forming a second transistor comprises the step of forming one of a second PFET and a second NFET.

5. (Original) The method of claim 4, wherein the step of forming one of a first PFET and a first NFET comprises forming one of a first PFET and a first NFET so that the sidewall of the first fin body is oriented on a second crystal plane to provide one of an optimized carrier mobility and a non-optimized carrier mobility, wherein the step of forming one of a second PFET and a second NFET comprises forming one of a second PFET and a second NFET so that the sidewall of the second fin body is oriented on a third crystal plane to provide one of an optimized carrier mobility and a non-optimized carrier mobility.

6. (Original) The method of claim 4, wherein the step of forming one of a first PFET and a first NFET comprises forming one of a first PFET and a first NFET so that the sidewall of the first fin body is oriented on one of a {100} crystal plane, a {110} crystal plane, and a {111} crystal plane, wherein the step of forming one of a second PFET and a second NFET comprises forming one of a second PFET and a second NFET so that the sidewall of the second fin body is oriented on one of a {100} crystal plane, a {110} crystal plane, and a {111} crystal plane.

7-19. (Canceled)